



STPS3045G

POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

I_{F(AV)}	30 A
V_{RRM}	45 V
T_j (max)	175°C
V_F (max)	0.63 V

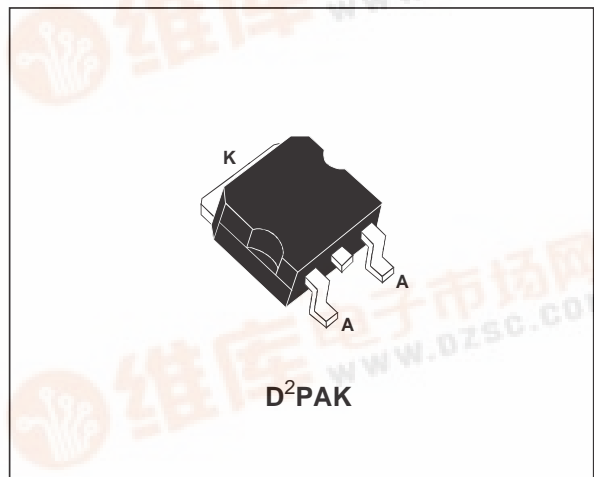
FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- EXTREMELY FAST SWITCHING
- LOW THERMAL RESISTANCE
- HIGH DISSIPATION MINIATURE PACKAGE
- AVALANCHE CAPABILITY SPECIFIED

DESCRIPTION

Single Schottky rectifier suited for switchmode power supply and high frequency DC to DC converters.

Packaged in D²PAK surface mount package, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
V _{RRM}	Repetitive peak reverse voltage	45	V
I _{F(RMS)}	RMS forward current	50	A
I _{F(AV)}	Average forward current	T _c = 150°C δ = 0.5 30	A
I _{FSM}	Surge non repetitive forward current	t _p = 10 ms Sinusoidal 200	A
I _{RRM}	Repetitive peak reverse current	t _p = 2 μs F = 1kHz square 1	A
I _{RSM}	Non Repetitive peak reverse current	t _p = 100 μs square 3	A
P _{ARM}	Repetitive peak avalanche power	t _p = 1 μs T _j = 25°C 6000	W
T _{stg}	Storage temperature range	- 65 to + 175	°C
T _j	Maximum operating junction temperature*	175	°C
dV/dt	Critical rate of rise of reverse voltage	10000	V/μs

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$ thermal runaway condition for a diode on its own heatsink



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THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case	1	$^{\circ}\text{C}/\text{W}$

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^{\circ}\text{C}$	$V_R = V_{RRM}$			500	μA
		$T_j = 125^{\circ}\text{C}$			20	80	mA
V_F^{**}	Forward voltage drop	$T_j = 125^{\circ}\text{C}$	$I_F = 30\text{ A}$		0.53	0.63	V
		$T_j = 25^{\circ}\text{C}$	$I_F = 60\text{ A}$			0.84	
		$T_j = 125^{\circ}\text{C}$	$I_F = 60\text{ A}$		0.68	0.78	

Pulse test : * $t_p = 5\text{ ms}$, $\delta < 2\%$
 ** $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation :
 $P = 0.48 \times I_{F(AV)} + 0.005 I_{F(RMS)}^2$

Fig. 1: Average forward power dissipation versus average forward current.

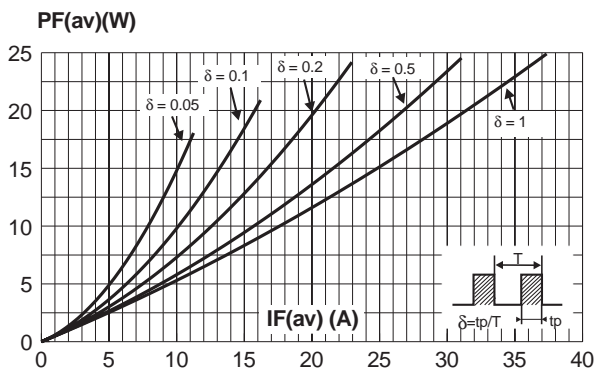


Fig. 3: Normalized avalanche power derating versus pulse duration.

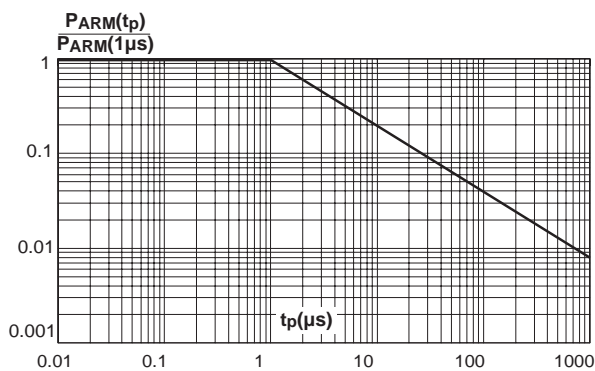


Fig. 2: Average forward current versus ambient temperature ($\delta=0.5$).

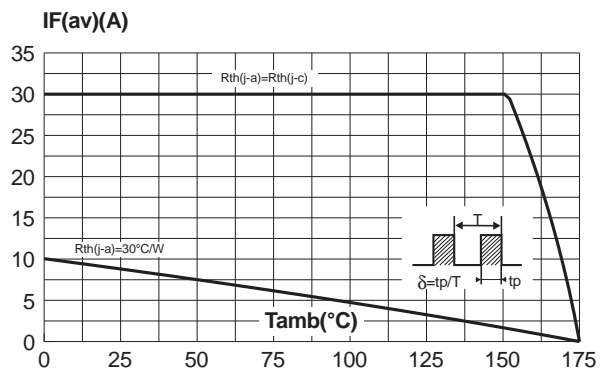


Fig. 4: Normalized avalanche power derating versus junction temperature.

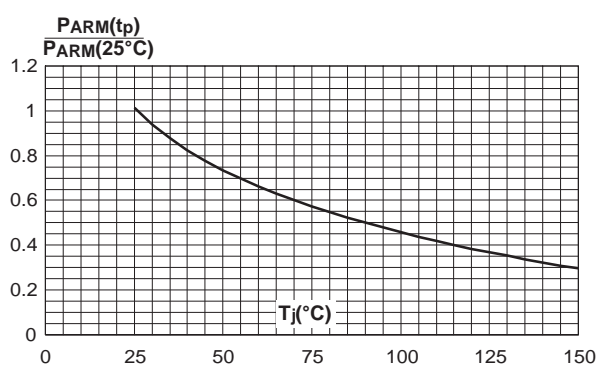


Fig. 5: Non repetitive surge peak forward current versus overload duration (maximum values).

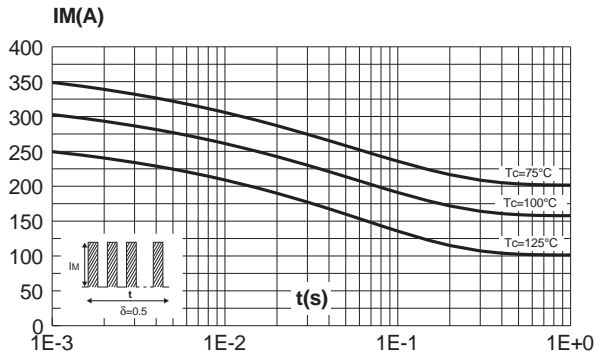


Fig. 6: Relative variation of thermal impedance junction to case versus pulse duration.

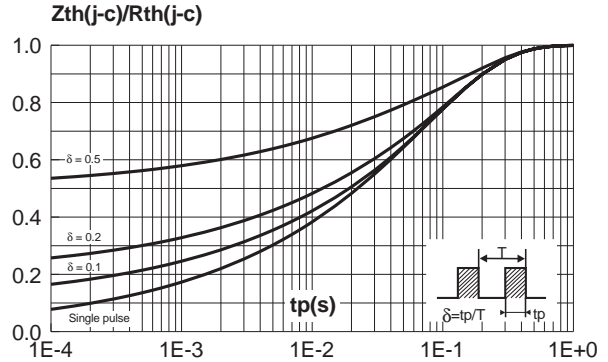


Fig. 7: Reverse leakage current versus reverse voltage applied (typical values)

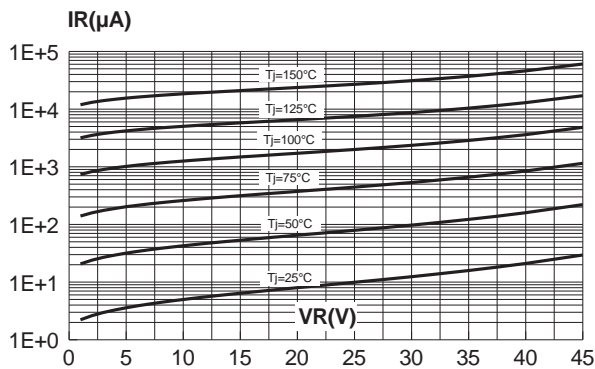


Fig. 8: Junction capacitance versus reverse voltage applied (typical values).

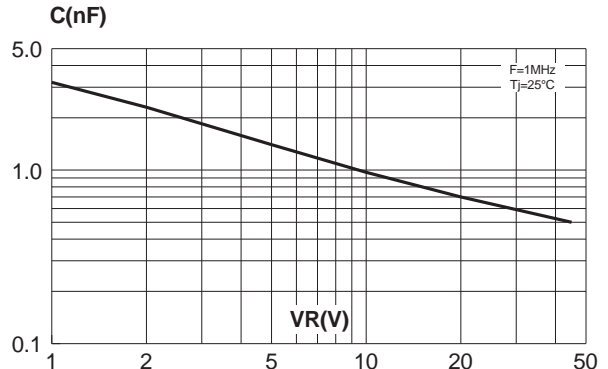


Fig. 9: Forward voltage drop versus forward current (maximum values).

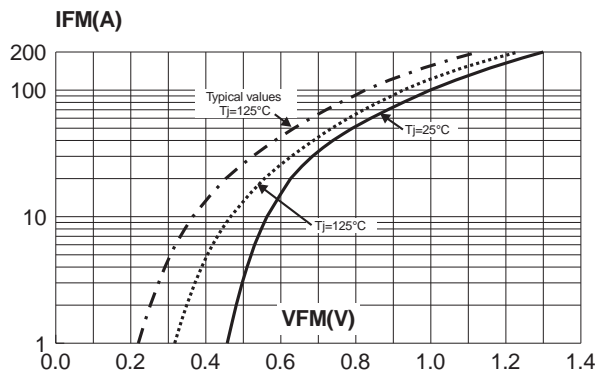
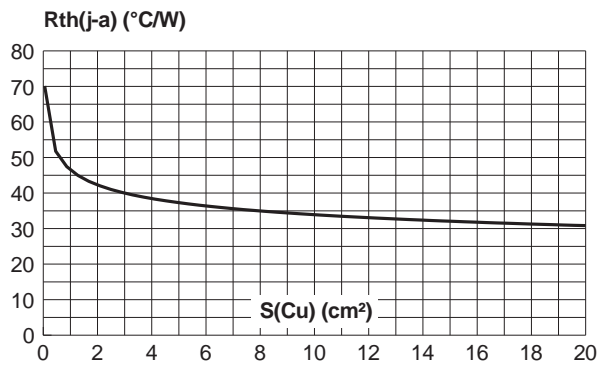
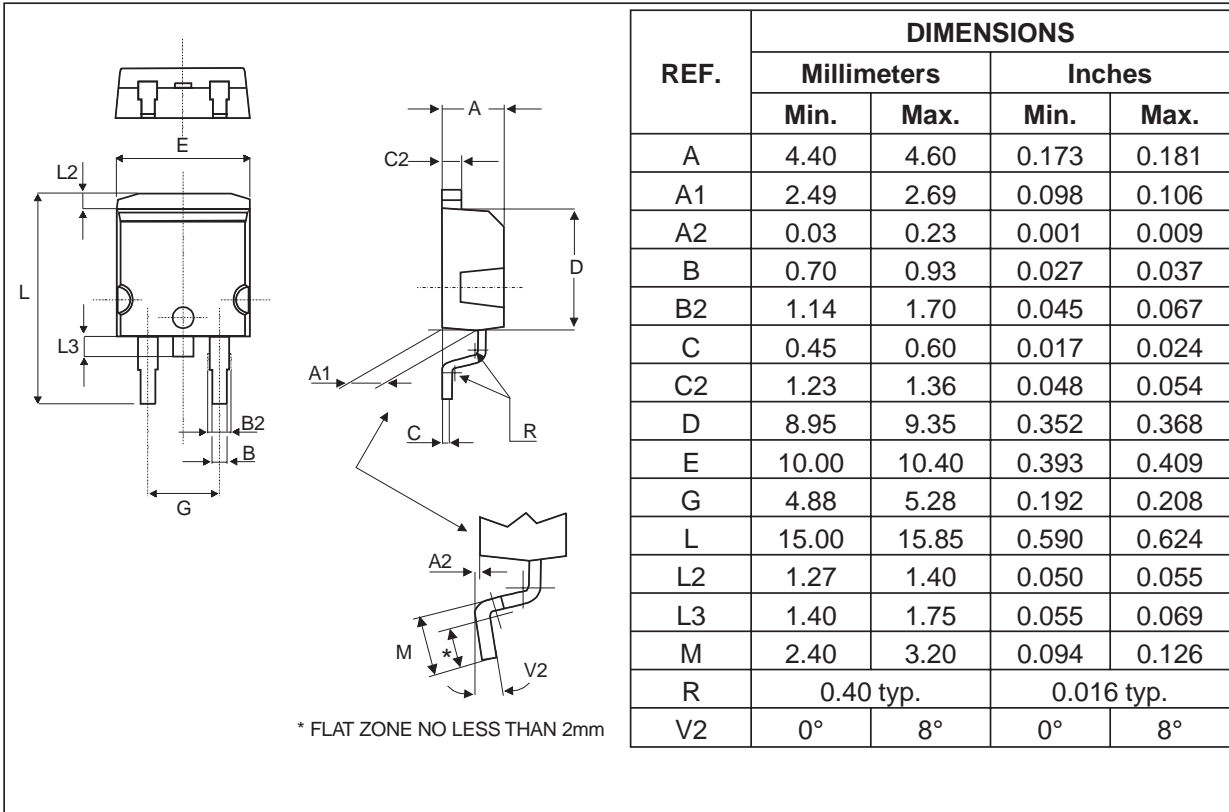


Fig. 10: Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board, copper thickness: 35µm)

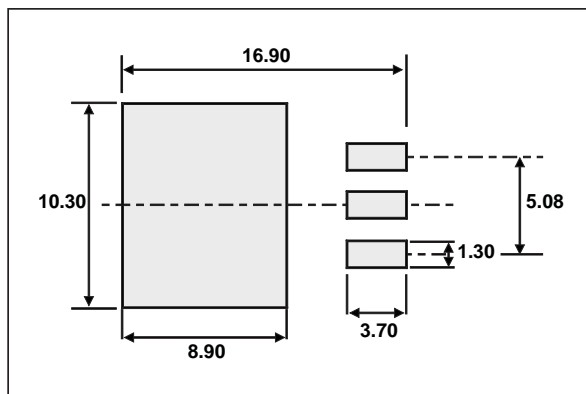


STPS3045G

PACKAGE MECHANICAL DATA D²PAK



FOOTPRINT DIMENSIONS (in millimeters)



Type	Marking	Package	Weight	Base qty	Delivery mode
STPS3045G	STPS3045G	D ² PAK	1.48g	50	Tube
STPS3045G-TR	STPS3045G	D ² PAK	1.48g	500	Tape & Reel

- Epoxy meets UL94, V0

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